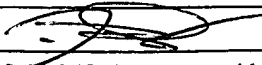


<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)  PTO Form 1449	Atty Docket No. 112857-534	Application No. 104512131
	Applicant Okuyama et al.	
	Filing Date October 21, 2004	Group 2815 Unknown

U.S. PATENT DOCUMENTS						
Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS								
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						Yes	No	
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②	Tachibana, K. et al., "Selective growth of InGaN quantum dot structures and their microphotoluminescence at room temperature," Applied Physics Letters, 29 May, 2000, Vol. 76, No. 22, pp. 3212-3214.	

Examiner: 	Date Considered: 12/19/04
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)  PTO Form 1449	Atty Docket No. 112857-534	Application No. 10/512,131
	Applicant Okuyama et al.	
	Filing Date 10/21/2004	Group 2815 <del>Unknown</del>

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						Yes	No
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	57-45583	03-15-82	Japan				
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Examiner: 

Date Considered: 12/19/06

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<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)  PTO Form 1449	Atty Docket No. 112857-534	Application No. 10/512,131
	Applicant Okuyama et al.	
	Filing Date 10/21/2004	Group 2815 <del>Unknown</del>

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<i>D</i>	Wang et al., "Fabrication of nanoscale structures of InGaN by MOCVD lateral overgrowth," Journal of Crystal Growth 197 (1999), pp. 48-53.

Examiner: <i>[Signature]</i>	Date Considered: 12/18/06
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